

Typical Characteristics

Electrical Characteristics (Ta=25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250 μA , V _{GS} =0	650	-	-	V
△BV _{DSS} /△T _J	Breakdown Voltage Temperature Coefficient	I _D =250 μA , Reference to 25 °C	-	0.67	-	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =650V, V _{GS} =0V	-	-	10	μA
		V _{DS} =520V, T _j =125°C			100	
I _{GSSF}	Gate-body leakage Current, Forward	V _{GS} =+30V, V _{DS} =0V	-	-	100	nA
I _{GSSR}	Gate-body leakage Current, Reverse	V _{GS} =-30V, V _{DS} =0V	-	-	-100	
On Characteristics						
V _{GS(TH)}	Date Threshold Voltage	I _D =250μA, V _{DS} =V _{GS}	2	-	4	V
R _{DS(ON)}	Static Drain-Source On-Resistance	I _D =2.0A, V _{GS} =10V	-		2.5	Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V , V _{GS} =0 , f=1.0MHz	-	560	-	pF
C _{oss}	Output Capacitance		-	48	-	
C _{rss}	Reverse Transfer Capacitance		-	5.4	-	
Switching Characteristics						
T _{d(on)}	Turn-On Delay Time	V _{DD} =325V , I _D =4A R _G =25Ω (Note 3,4)	-	25		nS
T _r	Turn-On Rise Time		-	45		
T _{d(off)}	Turn-Off Delay Time		-	25		
T _f	Turn-Off Rise Time		-	35		
Q _g	Total Gate Charge	V _{DS} =520V, V _{GS} =10V , I _D =4A (Note3,4)	-	14.3		nC
Q _{gs}	Gate-Source Charge		-	2.8	-	
Q _{gd}	Gate-Drain Charge		-	4.5	-	
Drain-Source Diode Characteristics and Maximum Ratings						
I _s	Max. Diode Forward Current	-		--	4	A
I _{SM}	Max. Pulsed Forward Current	-		--	16	
V _{SD}	Diode Forward Voltage	I _D =4A	-	-	1.4	V
T _{rr}	Reverse Recovery Time	I _s =4A, V _{GS} =0V diF/dt=100A/μs (Note3)	-	393	-	nS
Q _{rr}	Reverse Recovery Charge		-	1.5	-	μC

Notes : 1, L=0.5mH, IAS= 4A, VDD=50V, RG=25Ω , Starting TJ =25°C

2, Repetitive Rating : Pulse width limited by maximum junction temperature

3, Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%

4, Essentially Independent of Operating Temperature

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